

ABSTRACT OF THE DISCLOSURE

There is provided a semiconductor wafer treatment member in which the occurrence of slippage thereof is prevented and which has an adequate cohesiveness onto the semiconductor wafer and an excellent durability. The semiconductor wafer treatment member A of the present invention has at least a surface formed with a silicon carbide (SiC) film thereon, comprising a support portion for receiving a semiconductor wafer, said support portion being composed of salients with which said semiconductor wafer substantially comes into contact; and depressions formed with the silicon carbide (SiC) film to provide a coverage area between said salients, said salients being formed with top surfaces having a surface roughness Ra of $0.05\text{ }\mu\text{ m}$ to $1.3\text{ }\mu\text{ m}$.